

Form PTO-1449

Docket Number 299002048410

Application Number 09/904,162

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Applicant

Y. Tsuda, et al.

Filing Date July 11, 2001

Group Art Unit 2813

Mailing Date November 22, 2001

U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO

OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
Duplicate	1.	Sunakawa et al. (1997). "Thick GaN crystal growth with low defect density by hydride-vapor phase epitaxy" Ext. Abstract. (The 58th Autumn Meeting) J. Soc. of Appl. Phys. No. 1-266-2p-Q-15
	2.	Tanaka et al. (1997). "Reduced dislocation densities in selectivity-grown nitride materials" Ext. Abstract. (The 58th Autumn Meeting) J. Soc. of Appl. Phys. No. 1-265-2p-Q-14.

Ref # 1 on form 852 paper # 3

RECEIVED
JAN 19 2002
TO 2800 MAIL ROOM

EXAMINER:

DATE CONSIDERED:

1/20/04

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.